

# Multi Pixel Photon Counter (G-APD or Si-PMT) Hamamatsu Photonics

HAMAMATSU PHOTONICS K.K.



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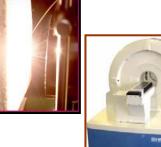
#### Solid Sate Division Electron Tube Division





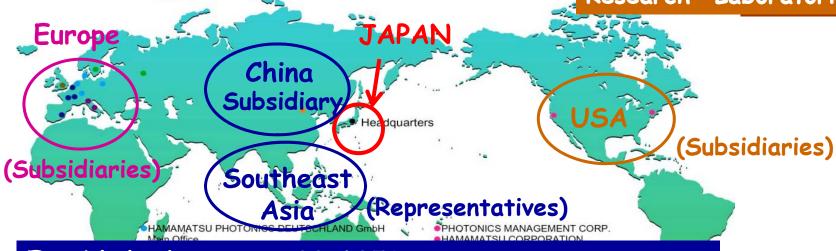






Systems Division

Research Laboratories



Established: Sept.29.1953

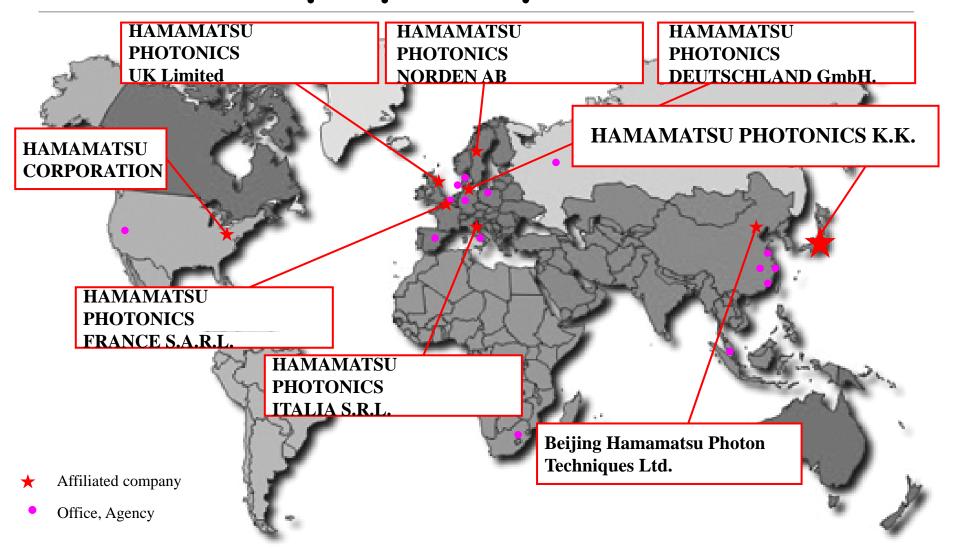
Net Sales: (FY 2011) Yen 100B (\$1.25B / €900M)

Employees: 4,000 (Group) (As of Sept.2011)

\80/\$ \110/€



### Worldwide propietary sales network



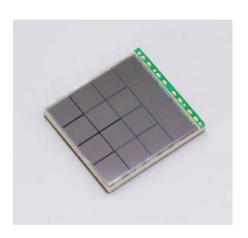


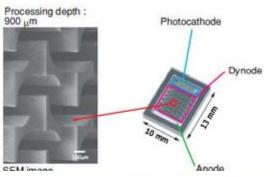
## MPPC is a G-APD (SiPMT)

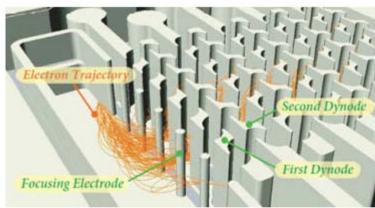
SiPMT is not a PMT SiPMT is an APD in Geiger mode



- small
- thin
- · MEMS applied technology
- · custom made flexibility
- · current PMT equivalent function









#### MPPC standard

#### ■ MPPC lineup (conventional type)

Туре	Metal type		Ceramic type		Plastic package (Surface mount type)			2D array type		
Image		TE-co	pooled					Array	Array	Array
Type no.	S10362-11 (-U series)	S11028 series	Preliminary	S10362-11 (-C series)	S10362-33 (-C series)	S10362-11 (-P series)	S10931 series	S10984 series	S10985 series	S11064 series
Effective active area	1 × 1 mm	1 × 1 mm	3 × 3 mm	1 × 1 mm	3 × 3 mm	1 × 1 mm	3 × 3 mm	1 × 4 mm (1 × 4ch array)	6 × 6 mm (2 × 2ch array)	3 × 3 mm/ch (4 × 4ch array)
	25 × 25	25 × 25	25 × 25	25 × 25	25 × 25	25 × 25	25 × 25	25 × 25	25 × 25	25 × 25
Pixel size (µm)	50 × 50	50 × 50	<b>50</b> × 50	50 × 50	50 × 50	50 × 50	50 × 50	50 × 50	50 × 50	
(pill)	100 × 100	100 × 100	100 × 100	100 × 100	100 × 100	100 × 100	100 × 100	100 × 100	100 × 100	50 × 50
Package	Metal (TO-18)	Metal (TO-8)	Metal (TO-8)	Ceramic	Ceramic	Plastic	Plastic	Plastic	Ceramic	Plastic



#### MPPC standard



#### Specifications (Typ. Ta=25 °C, unless otherwise noted)

	Symbol	S10362-11 series			
Parameter		-025U, -025C, -025P	-050U, -050C, -050P	-100U, -100C, -100P	Unit
Effective active area	-		1×1		mm
Number of pixels	-	1600	400	100	-
Pixel size	-	25 × 25	50 × 50	100 × 100	μm
Fill factor *1	-	30.8	61.5	78.5	%
Spectral response range	response range $\lambda$ 320 to 900		nm		
Peak sensitivity wavelength	λр	440			nm
Photon detection efficiency *2 (λ=λp)	PDE	25	50	65	%
Operating voltage range	-		70 ± 10 *3		V
Dark count *4	-	300	400	600	kcps
Dark count Max. *4	-	600	800	1000	kcps
Terminal capacitance	Ct	35			pF
Time resolution (FWHM) *5		200 to 300			ps
Temperature coefficient of reverse voltage -		56			
Gain	M	$2.75 \times 10^{5}$	$7.5 \times 10^{5}$	2.4 × 10 <sup>6</sup>	-

<sup>\*1:</sup> Ratio of the active area of a pixel to the entire area of the pixel

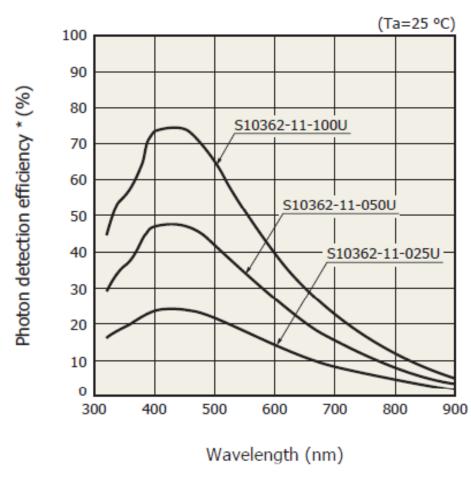
<sup>\*2:</sup> Photon detection efficiency includes effects of crosstalk and afterpulses.

<sup>\*3:</sup> For the recommended operating voltage of each product, refer to the data attached to each product.

<sup>\*4: 0.5</sup> p.e. (threshold level)



#### MPPC standard



<sup>\*</sup> Photon detection efficiency includes effects of crosstalk and afterpulses.



## MPPC. New products

NEW

NEW

NEW

**NEW** 

**Prototype** 

**4x4ch monolithic array** PWB package \$11827-3344MG



4x4ch monolithic array SMD package buttable S11828-3344M

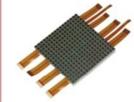


monolithic array with FPC (15 cm) buttable \$11829-3344MF

4x4ch



4x4ch monolithic array with FPC (5 cm) buttable S11830-3344MF



8x8ch discrete array with FPC buttable S11834-3388DF



## MPPC: Custom products

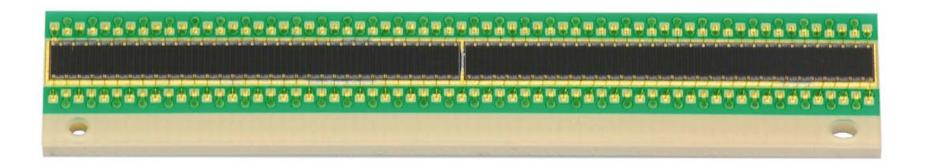
#### MPPC linear array 128ch - developed for fiber tracker

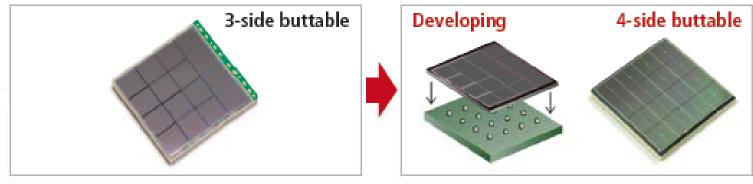
2 chips/assembly

Gap between active area of chips: 250um (= 1ch)

Buttable device (aimed gap : also 250um)

Thin epoxy layer: optimizing spatial resolution



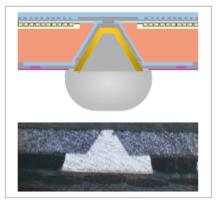


3 x 3 mm – 4 x 4 ch. 3 x 3 mm – 4 x 4 ch. monolithic array with wire bonding monolithic array with silicon through vias





#### Through Silicon Via (TSV)

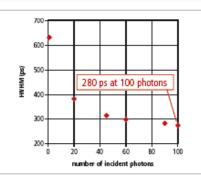


Cross section of TSV

#### 4-side buttable packaging

Large area monolithic arrays have been developed for TOF-PET. These have wire bonding pads at the edge of the chip only allowing a 3-side buttable assembly limiting the total size.

We have designed a monolithic array with through vias in which each channel has a bump pad and is connected by the shortest distance possible to the substrate. This 4-side buttable structure minimizes dead space and opens up new possibilities with its unlimited total size.



FWHM time resolution of 3 x 3 mm MPPC with TSV

#### Time resolution improvement

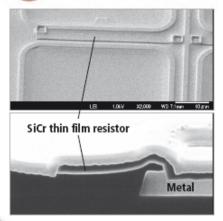
The large area monolithic array has long signal metal traces to the bonding pads

which add additional parasitic resistance and capacitance.

This causes a problem to obtain fast and uniform time response characteristics. The monolithic array with TSV has no traces and therefore it is possible to minimize the parasitic resistance and capacitance. The time resolution measurement was done with a picosecond light pulser. Timing of 280 ps was obtained with 3 x 3 mm single channel with an input of 100 photons. The TSV technology has advantages but needs further improvements to optimize the design and the process conditions to get best performance and total reliability.



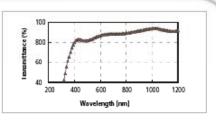
### 3 Thin metal film quenching resistor



Applying SiCr thin film
High energy physics (HEP) calorimetry
applications require photo sensors with
high dynamic range and high QE. MPPC
dynamic range depends on the pixel
density. However smaller pixels have lower
fill factor because of the space taken up
by the quenching resistors.
We have studied the use of SiCr thin film
resistors instead of poly-Si. It has higher
sheet resistance, a lower temperature coefficient and higher resistance uniformity
which allows for a more narrow pattern.

Material	TCR	Size	σ(Rs)	
Dalu Ci	-2.4 k Ω/°C	W=2 µm	20 %	
Poly-Si	-2.4 K \$2/°C	W=1 µm	39 %	
SiCr thin film	0.514.0000	W=2 μm	9 %	
SICI UIII IIIII	-0.5 K \$2/ C	W=1 µm	11 %	

This table provides a comparison of measurement data between poly-Si and SiCr resistors. The sheet resistance is 10 k Ohm/sq and the length is 60 mm. Temperature coefficient of resistance (TCR) and variation of resistance (s) in the wafer were drastically improved.



#### High transmittance

The area lost to the poly-Si quenching resistors formed around the active region limits the fill factor and QE The transmittance of SiCr thin film is more than 80 % in the range above 400 nm wavelength. It is possible to form the SiCr thin film resistor on top of the active area with minimal loss of sensitivity.

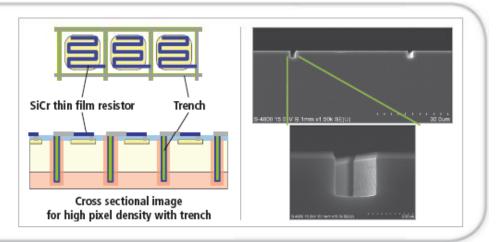




#### "All in one MPPCs"

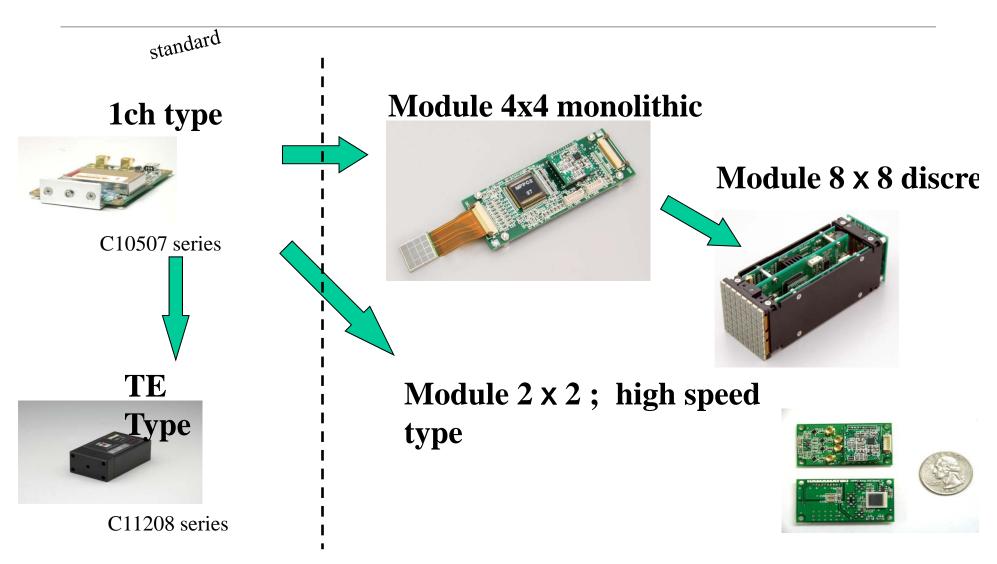
Decreasing optical cross talk has been one of the challenges for the MPPC. It is known that trenches formed around each elementary cell prevent stray photons from generating photoelectrons in neighboring cells. We are now processing 2 mm trenches (both width and depth) using a reactive ion-etching (RIE) machine. We have designed "All in one MPPCs" with these improved methods which

include TSV, SiCr thin film resistors, trench among others. One example is a large scale monolithic array MPPC in which the pixel pitch is 50 mm for TOF-PET applications. Another is a high pixel density MPPC with pixel pitches less than 15 mm for HEP applications. These experimental samples are in processing and initial characteristics will be obtained in a few months.



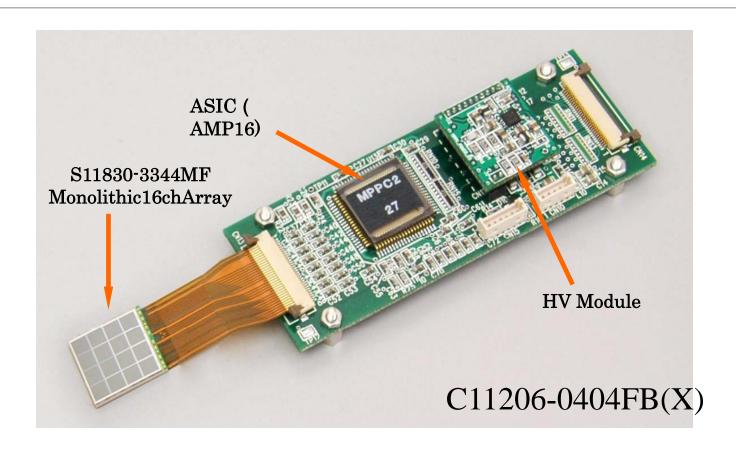


#### MPPC modules





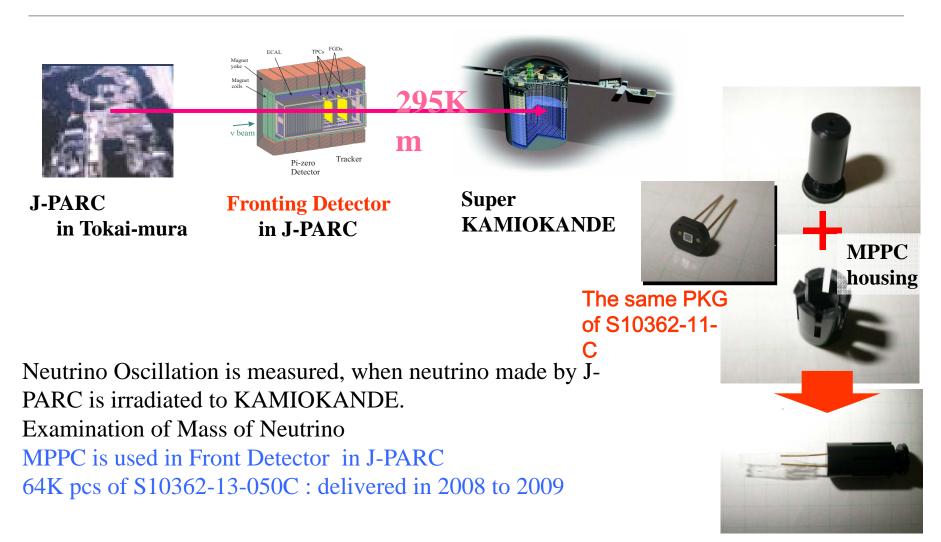
## MPPC module for 4x4 array



Including preamp and bias circuit for MPPC array



## In mass production since 2008



Kyoto Univ. present



# Thank you for your attention!!

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